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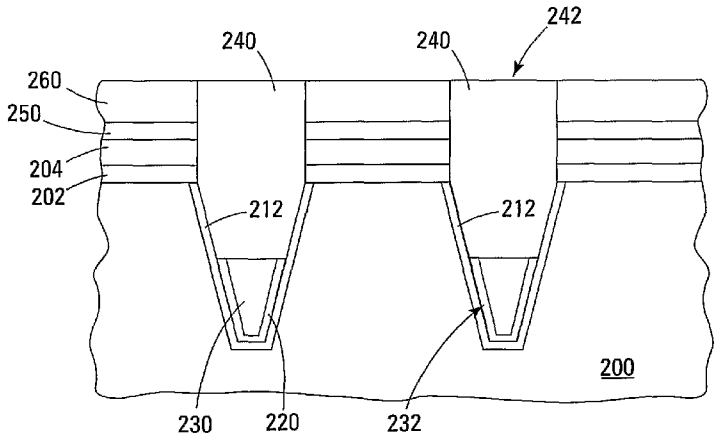
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(54) **Title:** ISOLATION TRENCHES FOR MEMORY DEVICES



(57) **Abstract:** Methods and apparatus are provided. A first dielectric plug is formed in a portion of a trench that extends into a substrate of a memory device so that an upper surface of the first dielectric plug is recessed below an upper surface of the substrate. The first dielectric plug has a layer of a first dielectric material and a layer of a second dielectric material formed on the layer of the first dielectric material. A second dielectric plug of a third dielectric material is formed on the upper surface of the first dielectric plug.

WO 2006/012163 A1